RJP30H1DPD

Silicon N Channel IGBT
High speed power switching

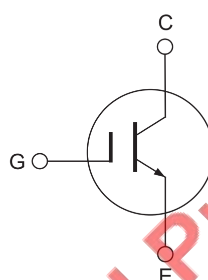
R07DS0465EJ0200
Rev.2.00
Jun 15, 2011

Features

- Trench gate and thin wafer technology (G6H-II series)
- High speed switching: t_r = 80 ns typ., t_f = 150 ns typ.
- Low collector to emitter saturation voltage: $V_{CE(sat)}$ = 1.5 V typ.
- Low leak current: I_{CES} = 1 μA max.

Outline

RENESAS Package code: PRSS0004ZJ-A
(Package name : TO-252)



1. Gate
2. Collector
3. Emitter
4. Collector (Flange)

EOL announced Product

Absolute Maximum Ratings

(Tc = 25°C)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	360	V
Gate to emitter voltage	V_{GES}	±30	V
Collector current	I_C	30	A
Collector peak current	ic(peak) Note1	200	A
Collector dissipation	P_C Note2	40	W
Junction to case thermal impedance	θj-c	3.13	°C/W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Tc = 25°C